

Amendments to the Claims

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1. (CURRENTLY AMENDED) A method of manufacturing a semiconductor device (10) with a substrate (1) and a semiconductor body (11) which comprises at least one active semiconductor element, wherein, after the semiconductor element has been formed, a layered structure is provided comprising at least one electrically insulating layer (2) or one electrically conductive layer (3), wherein an opening is formed in the layered structure by means of a patterned photoresist layer (4) and an etch process, wherein residues (6) are formed at the surface of the semiconductor body (11) during the etch process, wherein the photoresist layer (4) is ashed, after the etch process, by means of a treatment with an oxygen-containing compound, after which the surface of the semiconductor body (11) is cleaned using a cleaning agent containing a diluted solution of an acid in water and being heated to a temperature above room temperature, as a result of which the residues (6) formed are removed from the surface, characterized in that sulphuric acid is chosen for the acid in the cleaning agent.

2. (ORIGINAL) A method as claimed in claim 1, characterized in that a solution of exclusively sulphuric acid and demineralized water is chosen for the diluted solution of the acid.

3. (ORIGINAL) A method as claimed in claim 1, characterized in that a solution of sulphuric acid and phosphoric acid in demineralized water is chosen for the diluted solution of the acid.

4. (ORIGINAL) A method as claimed in claim 3, characterized in that the phosphoric acid concentration is chosen to range between 0.01 and 5% by weight, and preferably between 0.1 and 1 % by weight.

5. (CURRENTLY AMENDED) A method as claimed in ~~any one of the preceding claims~~ claim 1, characterized in that the sulphuric acid concentration is chosen to range between 0.01 and 10% by weight, and preferably between 0.5 and 5% by weight.

6. (CURRENTLY AMENDED) A method as claimed in ~~any one of the preceding claims~~ claim 1 characterized in that the temperature is chosen in the range between 20 and 60°C, and preferably between 30 and 45°C.

7. (CURRENTLY AMENDED) A method as claimed in ~~any one of the preceding claims~~ claim 1, characterized in that the cleaning operation is carried out for 2 to 30 minutes.

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